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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, MMC/SDIO, QSPI, SAI, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f413rht6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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2 Description

The STM32F413xG/H devices are based on the high-performance ARM[®] Cortex[®]-M4 32bit RISC core operating at a frequency of up to 100 MHz. Their Cortex[®]-M4 core features a Floating point unit (FPU) single precision which supports all ARM single-precision dataprocessing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F413xG/H devices belong to the STM32F4 access product lines (with products combining power efficiency, performance and integration) while adding a new innovative feature called Batch Acquisition Mode (BAM) allowing to save even more power consumption during data batching.

The STM32F413xG/H devices incorporate high-speed embedded memories (up to 1.5 Mbytes of Flash memory, 320 Kbytes of SRAM), and an extensive range of enhanced I/Os and peripherals connected to two APB buses, three AHB buses and a 32-bit multi-AHB bus matrix.

All devices offer a 12-bit ADC, two 12-bit DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timer for motor control, two general-purpose 32-bit timers and a low power timer.

They also feature standard and advanced communication interfaces.

- Up to four I²Cs, including one I²C supporting Fast-Mode Plus
- Five SPIs
- Five I²Ss out of which two are full duplex. To achieve audio class accuracy, the I²S peripherals can be clocked via a dedicate internal audio PLL or via an external clock to allow synchronization.
- Four USARTs and six UARTs
- An SDIO/MMC interface
- An USB 2.0 OTG full-speed interface
- Three CANs
- An SAI.

In addition, the STM32F413xG/H devices embed advanced peripherals:

- A flexible static memory control interface (FSMC)
- A Quad-SPI memory interface
- Two digital filter for sigma modulator (DFSDM) supporting microphone MEMs and sound source localization, one with two filters and up to four inputs, and the second one with four filters and up to eight inputs

They are offered in 7 packages ranging from 48 to 144 pins. The set of available peripherals depends on the selected package. Refer to *Table 2: STM32F413xG/H features and peripheral counts* for the peripherals available for each part number.

The STM32F413xG/H operate in the -40 to +125 °C temperature range from a 1.7 (PDR OFF) to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.



A dedicated application note (AN4515) describes how to implement the STM32F413xG/H BAM to allow the best power efficiency.

3.4 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 byte and the whole 4 Gbyte of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

3.5 Embedded Flash memory

The devices embed up to 1.5 Mbytes of Flash memory available for storing programs and data, plus 512 bytes of one-time programmable (OTP) memory organized in 16 blocks of 32 bytes, each which can be independently locked.

The user Flash memory area can be protected against read operations by an entrusted code (read protection or RDP). Different protection levels are available. The user Flash memory is divided into sectors, which can be individually protected against write operation. Flash sectors can also be protected individually against D-bus read accesses by using the proprietary readout protection (PCROP).

Refer to the product line reference manual for additional information on OTP area and protection features.

To optimize the power consumption the Flash memory can also be switched off in Run or in Sleep mode (see Section 3.20: Low-power modes).

Two modes are available: Flash in Stop mode or in DeepSleep mode (trade off between power saving and startup time.

Before disabling the Flash, the code must be executed from the internal RAM.

3.6 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.



3.18.1 Regulator ON

On packages embedding the BYPASS_REG pin, the regulator is enabled by holding BYPASS_REG low. On all other packages, the regulator is always enabled.

There are three power modes configured by software when the regulator is ON:

- MR is used in the nominal regulation mode (With different voltage scaling in Run mode) In Main regulator mode (MR mode), different voltage scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption.
- LPR is used in the Stop mode
 The LP regulator mode is configured by software when entering Stop mode.
- Power-down is used in Standby mode.

The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost.

Depending on the package, one or two external ceramic capacitors should be connected on the VCAP_1 and VCAP_2 pins. The VCAP_2 pin is only available on 100- and 144-pin packages.

All packages have the regulator ON feature.

3.18.2 Regulator OFF

This feature is available only on UFBGA100 and UFBGA144 packages, which feature the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V₁₂ voltage source through V_{CAP_1} and V_{CAP_2} pins.

Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency.

The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors.

When the regulator is OFF, there is no more internal monitoring on V_{12} . An external power supply supervisor should be used to monitor the V_{12} of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V_{12} power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V₁₂ logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.

	1	2	3	4	5	6	7	8	9	10	11	12
Α	PC13	PE3	PE2	PE1	PE0	PB4	PB3	PD6	PD7	PA15	PA14	PA13
в	PC14- OSC32_IN	PE4	PE5	PE6	PB9	PB5	PG15	PG12	PD5	PC11	PC10	PA12
с	PC15- OSC32_OUT	VBAT	PF0	PF1	PB8	PB6	PG14	PG11	PD4	PC12	VDDUSB	PA11
D	PH0 - OSC_IN	vss	VDD	PF2	BOOT0	PB7	PG13	PG10	PD3	PD1	PA10	PA9
E	PH1 - OSC_OUT	PF3	PF4	PF5	PDR_ON	VSS	VSS	PG9	PD2	PD0	PC9	PA8
F	NRST	PF7	PF6	VDD	VDD	VDD	VDD	VDD	VDD	VDD	PC8	PC7
G	PF10	PF9	PF8	VSS	VDD	VDD	VDD	VSS	VCAP_2	VSS	PG8	PC6
н	PC0	PC1	PC2	PC3	BYPASS_ REG	VSS	VCAP_1	PE11	PD11	PG7	PG6	PG5
J	VSSA	PA0	PA4	PC4	PB2	PG1	PE10	PE12	PD10	PG4	PG3	PG2
к	VREF-	PA1	PA5	PC5	PF13	PG0	PE9	PE13	PD9	PD13	PD14	PD15
L	VREF+	PA2	PA6	PB0	PF12	PF15	PE8	PE14	PD8	PD12	PB14	PB15
м	VDDA	PA3	PA7	PB1	PF11	PF14	PE7	PE15	PB10	PB11	PB12	PB13

Figure 17. STM32F413xG/H UFBGA144 pinout

1. The above figure shows the package top view.

Table 9. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition						
Pin name	Unless otherwise reset is the same	specified in brackets below the pin name, the pin function during and after as the actual pin name						
	S	Supply pin						
Pin type	I	Input only pin						
	I/O	Input/ output pin						
	FT	5 V tolerant I/O						
	FTf 5 V tolerant I/O, I2C FM+ option							
I/O atruatura	TC	Standard 3.3 V I/O						
	ТТа	3.3 V tolerant I/O directly connected to DAC						
	В	Dedicated BOOT0 pin						
	NRST	Bidirectional reset pin with embedded weak pull-up resistor						
Notes	Unless otherwise	specified by a note, all I/Os are set as floating inputs during and after reset						
Alternate functions	Functions selected							
Additional functions	Functions directly	Functions directly selected/enabled through peripheral registers						



	-	Р	in Nu	mber	-	-						
UFQFPN48	LQFP64	WLCSP81	LQFP100	UFBGA100	UFBGA144	LQFP144	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	9	C7	16	J2	H2	27	PC1	I/O	FT	-	LPTIM1_OUT, DFSDM2_DATIN4, SAI1_SD_B, EVENTOUT	ADC1_IN11, WKUP3
-	10	D7	17	J3	H3	28	PC2	I/O	FT	-	LPTIM1_IN2, DFSDM2_DATIN7, SPI2_MISO, I2S2ext_SD, SAI1_SCK_B, DFSDM1_CKOUT, FSMC_NWE, EVENTOUT	ADC1_IN12
-	11	E7	18	K2	H4	29	PC3	I/O	FT	-	LPTIM1_ETR, DFSDM2_CKIN7, SPI2_MOSI/I2S2_SD, SAI1_FS_B, FSMC_A0, EVENTOUT	ADC1_IN13
-	-	-	19	-	-	30	VDD	S	-	-	-	-
8	12	H9	20	J1	J1	31	VSSA	S	-	-	-	-
-	-	-	-	K1	K1	-	VREF-	S	-	-	-	-
-	-	G8	21	L1	L1	32	VREF+	S	-	-	-	-
9	13	F7	22	M1	M1	33	VDDA	S	-	-	-	-
10	14	G7	23	L2	J2	34	PA0	I/O	FT	-	TIM2_CH1/TIM2_ETR, TIM5_CH1, TIM8_ETR, USART2_CTS, UART4_TX, EVENTOUT	ADC1_IN0, WKUP1
11	15	H8	24	M2	K2	35	PA1	I/O	FT	-	TIM2_CH2, TIM5_CH2, SPI4_MOSI/I2S4_SD, USART2_RTS, UART4_RX, QUADSPI_BK1_IO3, EVENTOUT	ADC1_IN1
12	16	J9	25	К3	L2	36	PA2	I/O	FT	-	TIM2_CH3, TIM5_CH3, TIM9_CH1, I2S2_CKIN, USART2_TX, FSMC_D4/FSMC_DA4, EVENTOUT	ADC1_IN2
13	17	E6	26	L3	M2	37	PA3	I/O	FT	-	TIM2_CH4, TIM5_CH4, TIM9_CH2, I2S2_MCK, USART2_RX, SAI1_SD_B, FSMC_D5/FSMC_DA5, EVENTOUT	ADC1_IN3

Table 10. STM32F413xG/H pin definition (continued)



		Р	in Nu	mber								
UFQFPN48	LQFP64	WLCSP81	LQFP100	UFBGA100	UFBGA144	LQFP144	Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
28	36	H1	54	K10	L12	76	PB15	I/O	FTf	-	RTC_REFIN, TIM1_CH3N, TIM8_CH3N, I2CFMP1_SCL, SPI2_MOSI/I2S2_SD, DFSDM1_CKIN2, TIM12_CH2, SDI0_CK, EVENTOUT	-
-	-	NC	55	-	L9	77	PD8	I/O	FT	(2)	USART3_TX, FSMC_D13/FSMC_DA1 3, EVENTOUT	-
-	-	F2	56	K8	K9	78	PD9	I/O	FT	-	USART3_RX, FSMC_D14/FSMC_DA1 4, EVENTOUT	-
-	-	G1	57	J12	Jð	79	PD10	I/O	FT	(7)	USART3_CK, UART4_TX, FSMC_D15/FSMC_DA1 5, EVENTOUT	-
-	-	NC	58	J11	H9	80	PD11	I/O	FT	(2)	DFSDM2_DATIN2, I2CFMP1_SMBA, USART3_CTS, QUADSPI_BK1_IO0, FSMC_A16, EVENTOUT	-
-	-	NC	59	J10	L10	81	PD12	I/O	FTf	(2)	TIM4_CH1, DFSDM2_CKIN2, I2CFMP1_SCL, USART3_RTS, QUADSPI_BK1_IO1, FSMC_A17, EVENTOUT	-
-	-	NC	60	H12	K10	82	PD13	I/O	FTf	(2)	TIM4_CH2, I2CFMP1_SDA, QUADSPI_BK1_IO3, FSMC_A18, EVENTOUT	-
-	-	-	-	-	G8	83	VSS	S	-	-	-	-
-	-	-	-	-	F8	84	VDD	S	-	-	-	-
-	-	NC	61	H11	K11	85	PD14	I/O	FTf	(2)	TIM4_CH3, I2CFMP1_SCL, DFSDM2_CKIN0, UART9_RX, FSMC_D0/FSMC_DA0, EVENTOUT	-

Table 10. STM32F413xG/H pin definition (continued)



Bus	Boundary address	Peripheral				
	0xE010 0000 - 0xFFFF FFFF	Reserved				
Cortex [®] -M4	0xE000 0000 - 0xE00F FFFF	Cortex-M4 internal peripherals				
	0xA000 2000 - 0xDFFF FFFF	Reserved				
	0xA000 1000 - 0xA000 1FFF	QuadSPI control register				
	0xA000 0000 - 0xA000 0FFF	FSMC control register				
АПЬЗ	0x9000 0000 - 0x9FFF FFFF	QUADSPI				
	0x7000 0000 - 0x08FFF FFFF	Reserved				
	0x6000 0000 - 0x6FFF FFFF	FSMC				
	0x5006 0C00 - 0x5FFF FFFF	Reserved				
	0x5006 0800 0x5006 0BFF	RNG				
AHB2	0x5004 0000 - 0x5006 07FF	Reserved				
	0x5000 0000 - 0x5003 FFFF	USB OTG FS				
	0x4002 6800 - 0x4FFF FFFF	Reserved				
	0x4002 6400 - 0x4002 67FF	DMA2				
	0x4002 6000 - 0x4002 63FF	DMA1				
	0x4002 4000 - 0X4002 5FFF	Reserved				
	0x4002 3C00 - 0x4002 3FFF	Flash interface register				
	0x4002 3800 - 0x4002 3BFF	RCC				
	0x4002 3400 - 0x4002 37FF	Reserved				
	0x4002 3000 - 0x4002 33FF	CRC				
AHB1	0x4002 2000 - 0x4002 2FFF	Reserved				
	0x4002 1C00 - 0x4002 1FFF	GPIOH				
	0x4002 1800 - 0x4002 1BFF	GPIOG				
	0x4002 1400 - 0x4002 17FF	GPIOF				
	0x4002 1000 - 0x4002 13FF	GPIOE				
	0x4002 0C00 - 0x4002 0FFF	GPIOD				
	0x4002 0800 - 0x4002 0BFF	GPIOC				
	0x4002 0400 - 0x4002 07FF	GPIOB				
	0x4002 0000 - 0x4002 03FF	GPIOA				

Table 13. STM32F413xG/H register boundary addresses





Bus	Boundary address	Peripheral
	0x4001 6800- 0x4001 FFFF	Reserved
	0x4001 6400 - 0x4001 67FF	DFSDM2
	0x4001 6000 - 0x4001 63FF	DFSDM1
	0x4001 5C00 - 0x4001 5FFF	Reserved
	0x4001 5800 - 0x4001 5BFF	SAI1
	0x4001 5400 - 0x4001 57FF	Reserved
	0x4001 5000 - 0x4001 53FF	SPI5/I2S5
	0x4001 4C00 - 0x4001 4FFF	Reserved
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	TIM9
	0x4001 3C00 - 0x4001 3FFF	EXTI
APB2	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	SPI4/I2S4
	0x4001 3000 - 0x4001 33FF	SPI1/I2S1
	0x4001 2C00 - 0x4001 2FFF	SDIO
	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1/2/3
	0x4001 1C00 - 0x4001 1FFF	UART10
	0x4001 1800 - 0x4001 1BFF	UART9
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0800 - 0x4001 0FFF	Reserved
	0x4001 0400 - 0x4001 07FF	TIM8
	0x4001 0000 - 0x4001 03FF	TIM1

Table 13. STM32F413xG/H register boundary addresses (continued



M)		enabled except pielett	in runn	ing non	1 1 10311 11	iemory	/- •DD •	- J.J V	
			f	Тур		Ma	x ⁽¹⁾		
Symbol	Parameter	Conditions	'HCLK (MHz)	T _A = 25 °C	T _A = 25 °C	T _A = 85 ℃	T _A = 105 °C	T _A = 125 °C	Unit
			100	30.7	32.85 ⁽⁴⁾	33.30	35.37	39.08	
			84	24.7	26.48	27.15	28.94	32.65	
		External clock,	64	17.2	18.36	19.14	20.88	24.29	
		all peripherals enabled ⁽³⁾	50	13.6	14.54	15.45	17.27	20.58	
			25	7.4	7.97	9.23	11.05	14.42	- mA
			20	6.4	6.99	8.18	10.03	13.32	
		HSI, PLL OFF, all peripherals enabled ⁽³⁾	16	4.5	5.04	6.32	8.23	11.50	
1	Supply current		1	1.0	1.50	2.89	4.59	8.01	
'DD	in Run mode		100	13.1	14.36	15.33	17.25	20.98	
			84	10.7	11.67	12.73	14.56	18.21	
		External clock, PLL ON ⁽²⁾	64	7.5	8.23	9.40	11.13	14.52	1
		all peripherals disabled ⁽³⁾	50	6.1	6.74	7.89	9.61	12.98	
			25	3.5	4.19	5.37	7.08	10.48	
			20	3.2	3.71	5.02	6.72	10.15	
		HSI, PLL OFF, all	16	2.1	2.67	3.95	5.84	9.10	
		peripherals disabled ⁽³⁾	1	0.8	1.35	2.72	4.43	7.87	

Table 26. Typical and maximum current consumption in run mode, code with data processing(ART accelerator enabled except prefetch) running from Flash memory - V_{DD} = 3.6 V

1. Guaranteed by characterization results.

2. Refer to Table 47 and RM0383 for the possible PLL VCO setting

3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).

4. Tested in production.



			_	Тур		Ma	x ⁽¹⁾		Unit
Symbol	Parameter	Conditions	f _{HCLK} (MHz)	T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	T _A = 125 °C	
			100	36.1	38.48	39.08	40.91	44.59	
		Extornal clock	84	30.6	32.60	33.14	35.10	38.56	
		PLL ON,	64	23.9	25.67	26.27	27.94	31.19	
		all peripherals	50	18.9	20.32	21.04	22.85	26.10	
		enabled	25	10.8	11.63	12.75	14.56	17.87	mA
			20	9.2	9.84	11.06	12.98	16.23	
		HSI, PLL OFF, all peripherals enabled ⁽²⁾⁽³⁾	16	7.1	7.69	9.02	10.87	14.25	
امم	Supply current		1	1.2	1.84	3.10	4.84	8.20	
66	in Run mode		100	18.6	20.33	21.23	23.15	26.71	
			84	16.5	18.09	19.01	20.81	24.29	
		External clock, PLL ON ⁽³⁾	64	14.3	15.76	16.67	18.28	21.50	
		all peripherals disabled	50	11.5	12.57	13.53	15.33	18.49	
			25	7.0	7.67	8.90	10.76	14.05	
			20	6.0	6.68	7.87	9.65	12.96	
		HSI, PLL OFF,	16	4.8	5.33	6.66	8.49	11.86	
		all peripherals disabled ^{(3)}	1	1.0	1.62	2.95	4.66	8.06	

Table 28. Typical and maximum current consumption in run mode, code with data processing
(ART accelerator disabled) running from Flash memory - V_{DD} = 1.7 V

1. Guaranteed by characterization results.

2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).

3. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.



On-chip peripheral current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- The ART accelerator is ON.
- Voltage Scale 2 mode selected, internal digital voltage V12 = 1.26 V.
- HCLK is the system clock at 100 MHz. f_{PCLK1} = f_{HCLK}/2, and f_{PCLK2} = f_{HCLK}.
 The given value is calculated by measuring the difference of current consumption
 - with all peripherals clocked off,
 - with only one peripheral clocked on,
 - scale 1 with f_{HCLK} = 100 MHz,
 - scale 2 with f_{HCLK} = 84 MHz,
 - scale 3 with f_{HCLK} = 64 MHz.
- Ambient operating temperature is 25 °C and V_{DD}=3.3 V.

Table 39. Peripheral current	consumption
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Perinheral			Unit			
renpi	eidi	Scale 1	Scale 2	Scale 3	Unit	
	GPIOA	1.89	1.82	1.64		
	GPIOB	1.75	1.68	1.52		
	GPIOC	1.70	1.64	1.48		
	GPIOD	1.72	1.65	1.48		
	GPIOE	1.78	1.71	1.55	µA/MHz	
AHB1	GPIOF	1.68	1.62	1.45		
	GPIOG	1.66	1.61	1.44		
	GPIOH	0.72	0.69	0.63		
	CRC	0.30	0.30	0.28		
	DMA1 ⁽¹⁾	1.75N + 3.14	1.66N + 3.00	1.49N + 2.70		
	DMA2 ⁽¹⁾	1.79N + 3.29	1.71N + 3.14	1.53N + 2.82		
AHB2	RNG	0.72	0.70	0.63		
	USB_OTG_FS	19.26	18.37	16.47	μΑνινιτΖ	
	FSMC	5.42	5.18	4.64		
AHB3	QSPI	10.33	9.86	8.84	µA/MHZ	



Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ ⁽¹⁾	Max ⁽¹⁾	Unit	
t _{WUSLEEP}	Wakeup from Sloop mode	-	-	4	6	clk cycles	
t _{WUSLEEPFDSM}	wakeup from Sleep mode	Flash memory in Deep power down mode	-	-	50.0		
		Main regulator	-	12.7	15.0		
		Main regulator, Flash memory in Deep power down mode	-	104.1	120.0	0	
twustop	Wakeup from STOP mode Code execution on Flash	Wakeup from Stop mode, regulator in low power mode ⁽²⁾	-	20.9	28.0		
		Regulator in low power mode, Flash memory in Deep power down mode ⁽²⁾	-	112.5	130.0	30.0	
		Regulator in low power mode low voltage, Flash memory in Deep power down mode	-	112.5	130.0	μs	
	Wakeup from STOP mode	Main regulator with Flash in Stop mode or Deep power down ⁽²⁾	-	4.2	7.0		
twustop	code execution on RAM ⁽³⁾	Wakeup from Stop mode, regulator in low power mode and Flash in Stop mode or Deep power down	-	12.6	20.0		
twustdby	Wakeup from Standby mode	-	-	328.2	400.0		
		From Flash_Stop mode	-	-	11.0		
^t WUFLASH	Wakeup of Flash	From Flash Deep power down mode	-	-	40.0		

Table 40. Low-power mode wakeup timings ⁽	1)
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1. Guaranteed by characterization results.

2. The specification is valid for wakeup from regulator in low power mode or low power low voltage mode, since the timing difference is negligible.

3. For the faster wakeup time for code execution on RAM, the Flash must be in STOP or DeepPower Down mode (see reference manual RM0430).

6.3.8 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the *Table 59*. However, the recommended clock input waveform is shown in *Figure 27*.



Low-speed internal (LSI) RC oscillator

Symbol	Parameter	Min	Тур	Мах	Unit
f _{LSI} ⁽²⁾	Frequency	16.1	32.0	47.0	kHz
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	15.0	40.0	μs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	0.4	0.6	μA

1. V_{DD} = 3 V, T_A = -40 to 125 °C unless otherwise specified.

2. Guaranteed by characterization results.

3. Guaranteed by design.



Figure 32. ACC_{LSI} versus temperature



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f _{PLL_IN}	PLL input clock ⁽¹⁾	-	-		1	2.10	
f _{PLLI2SQ_OUT}	48 MHz PLLI2SQ multiplier output clock	-		-	48	75	MU-7
f _{PLLI2SR_OUT}	PLLI2SR multiplier output clock for I2S and SAI	-		-	-	216	
f _{VCO_OUT}	PLLI2S VCO output	-		100	-	432	
		VCO freq = 100 MHz		75	-	200	
LOCK		VCO freq = 432 MHz		100	-	300	μs
Jitter ⁽³⁾	Maataa 100 alaak iittaa	Cycle to cycle at	RMS	-	90	-	
		12.288 MHz on 48 kHz period, N=432, R=5	peak to peak	-	±280	-	
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples		-	90	-	ps
	WS I2S clock jitter	Cycle to cycle at 48 KHz on 1000 samples		-	400	-	
I _{DD(PLLI2S)} ⁽⁴⁾	PLLI2S power consumption on V_{DD}	VCO freq = 100 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	m۸
I _{DDA(PLLI2S)} ⁽⁴⁾	PLLI2S power consumption on V _{DDA}	VCO freq = 100 MHz VCO freq = 432 MHz	<u>.</u>	0.30 0.55	-	0.40 0.85	

Table 48. PLLI2S	(audio PLL)) characteristics

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.

2. Guaranteed by design.

3. Value given with main PLL running.

4. Guaranteed by characterization results.



Figure 33 and *Figure 34* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

 T_{mode} is the modulation period.

md is the modulation depth.









6.3.12 Memory characteristics

Flash memory

The characteristics are given at T_A = -40 to 125 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

Table	50.	Flash	memory	characteristics
Table	50.	i iasii	III CIII OI Y	Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		Write / Erase 8-bit mode, V_{DD} = 1.7 V	-	5	-	
I _{DD} Supply current	Supply current	Write / Erase 16-bit mode, V_{DD} = 2.1 V	-	8	-	mA
		Write / Erase 32-bit mode, V_{DD} = 3.3 V	-	12	-	

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Figure 35. FT/TC I/O input characteristics

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14 and PC15 which can sink or source up to ± 3 mA. When using the PC13 to PC15 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in Section 6.2. In particular:

- The sum of the currents sourced by all the I/Os on V_{DD}, plus the maximum Run consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 15*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 15*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 60* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*. All I/Os are CMOS and TTL compliant.



General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 50* or *Figure 51*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.





1. V_{REF+} and V_{REF-} inputs are both available on UFBGA100. V_{REF+} is also available on LQFP100. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA} .



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _{wh(CKIN)} t _{wl(CKIN)}	Input clock high and low time	SPI mode (SITP[1:0] = 01), External clock mode (SPICKSEL[1:0] = 0) 1.71 < V _{DD} < 3.6 V	t _{CKIN} / 2 - 0.5	t _{CKIN} / 2	-	
t _{su}	Data input setup time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0) 1.71 < V _{DD} < 3.6 V	3.5	-	-	
t _h	Data input hold time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0) 1.71 < V _{DD} < 3.6 V	2.5	-	-	ns
T _{Manchester}	Manchester data period (recovered clock period)	Manchester mode (SITP[1:0] = 10 or 11), Internal clock mode (SPICKSEL[1:0] \neq 0) 1.71 < V _{DD} < 3.6 V	(CKOUTDIV + 1) ^{* t} DFBDMCLK	-	(2 * CKOUTDIV) * t _{DFBDMCLK}	

Table 87. DFSDM characteristics⁽¹⁾ (continued)

1. Data based on characterization results.



Symbol	Parameter	Min	Мах	Unit
t _{w(CLK)}	FSMC_CLK period, V _{DD} range= 2.7 to 3.6 V	2 * T _{HCLK} - 0.5	-	
t _{d(CLKL-NExL)}	FSMC_CLK low to FSMC_NEx low (x= 02)	-	2	
t _{d(CLKH-NExH)}	FSMC_CLK high to FSMC_NEx high (x= 02)	T _{HCLK} + 0.5	-	
t _{d(CLKL-NADVL)}	FSMC_CLK low to FSMC_NADV low	-	1	
t _{d(CLKL-NADVH)}	FSMC_CLK low to FSMC_NADV high	0	-	
t _{d(CLKL-AV)}	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	2.5	
t _{d(CLKH-AIV)}	FSMC_CLK high to FSMC_Ax invalid (x=1625)	T _{HCLK}	-	
t _{d(CLKL-NWEL)}	FSMC_CLK low to FSMC_NWE low	-	1.5	
t _(CLKH-NWEH)	FSMC_CLK high to FSMC_NWE high	T _{HCLK} + 0.5	-	115
t _{d(CLKL-ADV)}	FSMC_CLK low to FSMC_AD[15:0] valid	-	3	
t _{d(CLKL-ADIV)}	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	
t _{d(CLKL-DATA)}	FSMC_A/D[15:0] valid data after FSMC_CLK low	-	4	
t _{d(CLKL-NBLL)}	FSMC_CLK low to FSMC_NBL low	0	2	
t _{d(CLKH-NBLH)}	FSMC_CLK high to FSMC_NBL high	T _{HCLK} + 0.5	-	
t _{su(NWAIT-CLKH)}	FSMC_NWAIT valid before FSMC_CLK high	2	-	
t _{h(CLKH-NWAIT)}	FSMC_NWAIT valid after FSMC_CLK high	3.5	-	

Table 97. S	vnchronous	multiplexed	PSRAM	write	timings ⁽¹⁾⁽²⁾

1. C_L = 30 pF.

2. Guaranteed by characterization results.

